

1A 40V(0.82mm)

**Chip Information**

Chip Size	0.82 x 0.82mm
Pad Size	0.68 x 0.68mm
Chip Quantity	16276 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	1000	mA	
Peak Forward Surge Current	IFSM	10	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.550		0.480	V	IF=1000mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	200	100	8	uA	VR=42V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	42	44	51	V	IR=80uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

**Ordering Information**

Chip Type	Chip Thickness	Back Metal
XHH515	180 +/- 20um	Au(For Eutectic)
XHH517	150 +/- 20um	Au(For Eutectic)
XHH516	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:

Designed For 1N5818,1N5819,1SS349